

SiC

Silicon Carbide Diode

5th Generation thinQ!TM

650V SiC Schottky Diode
IDW30G65C5

Final Datasheet

Rev. 2.0 <2012-06-28>

Power Management & Multimarket

5th Generation thinQ!™ SiC Schottky Diode

1 Description

ThinQ!™ Generation 5 represents Infineon leading edge technology for the SiC Schottky Barrier diodes. Thanks to the more compact design and thin-wafer technology, the new family of products shows improved efficiency over all load conditions, resulting from both the improved thermal characteristics and a lower figure of merit ($Q_c \times V_f$).

The new thinQ!™ Generation 5 has been designed to complement our 650V CoolMOS™ families: this ensures meeting the most stringent application requirements in this voltage range.

Features

- Revolutionary semiconductor material - Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Optimized for high temperature operation

Benefits

- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI

Applications

- Switch mode power supply
- Power factor correction
- Solar inverter
- Uninterruptible power supply

Table 1 Key Performance Parameters

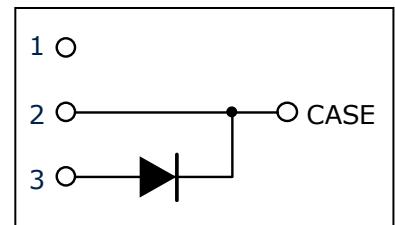
| Parameter | Value | Unit |
|---------------------------|-------|------|
| V_{DC} | 650 | V |
| $Q_C; V_R=400V$ | 42 | nC |
| $E_C; V_R=400V$ | 10.5 | μJ |
| $I_F @ T_C < 115^\circ C$ | 30 | A |

Table 2 Pin Definition

| Pin 1 | Pin 2 | Pin 3 |
|-------|-------|-------|
| n.c. | C | A |

| Type / ordering Code | Package | Marking | Related links |
|----------------------|------------|---------|--|
| IDW30G65C5 | PG-TO247-3 | D3065C5 | www.infineon.com/sic |

IDW30G65C5



1) J-STD20 and JESD22

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2 Maximum ratings

Table 3 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note/Test Condition |
|---|----------------|--------|------|------|------------------|--|
| | | Min. | Typ. | Max. | | |
| Continuous forward current | I_F | – | – | 30 | A | $T_C < 115^\circ\text{C}$, $D=1$ |
| Surge non-repetitive forward current, sine halfwave | $I_{F,SM}$ | – | – | 165 | | $T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$ |
| | | – | – | 139 | | $T_C = 150^\circ\text{C}$, $t_p=10\text{ ms}$ |
| Non-repetitive peak forward current | $I_{F,max}$ | – | – | 1106 | | $T_C = 25^\circ\text{C}$, $t_p=10\text{ }\mu\text{s}$ |
| i ² t value | $\int i^2 dt$ | – | – | 136 | A ² s | $T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$ |
| | | – | – | 97 | | $T_C = 150^\circ\text{C}$, $t_p=10\text{ ms}$ |
| Repetitive peak reverse voltage | V_{RRM} | – | – | 650 | V | |
| Diode dv/dt ruggedness | dv/dt | – | – | 100 | V/ns | $V_R=0..480\text{ V}$ |
| Power dissipation | P_{tot} | – | – | 150 | W | $T_C = 25^\circ\text{C}$ |
| Operating and storage temperature | $T_j; T_{stg}$ | -55 | – | 175 | °C | |
| Mounting torque | | – | 50 | 70 | Ncm | M3 and M4 screws |

3 Thermal characteristics

Table 4 Thermal characteristics TO-247-3

| Parameter | Symbol | Values | | | Unit | Note/Test Condition |
|--|------------|--------|------|------|------|--------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction-case | R_{thJC} | – | 0.8 | 1.0 | K/W | |
| Thermal resistance, junction-ambient | R_{thJA} | – | – | 62 | | leaded |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | – | – | 260 | °C | 1.6mm (0.063 in.) from case for 10 s |

4 Electrical characteristics

Table 5 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note/Test Condition |
|-----------------------|----------|--------|------|-------|---------------|--|
| | | Min. | Typ. | Max. | | |
| DC blocking voltage | V_{DC} | 650 | – | – | V | $I_R = 5.2 \text{ mA}, T_j = 25^\circ\text{C}$ |
| Diode forward voltage | V_F | – | 1.5 | 1.8 | | $I_F = 30 \text{ A}, T_j = 25^\circ\text{C}$ |
| | | – | 1.8 | 2.2 | | $I_F = 30 \text{ A}, T_j = 150^\circ\text{C}$ |
| Reverse current | I_R | – | 1.6 | 5200 | μA | $V_R = 650 \text{ V}, T_j = 25^\circ\text{C}$ |
| | | – | 0.4 | 1350 | | $V_R = 600 \text{ V}, T_j = 25^\circ\text{C}$ |
| | | – | 6.1 | 19800 | | $V_R = 650 \text{ V}, T_j = 150^\circ\text{C}$ |

Table 6 AC characteristics

| Parameter | Symbol | Values | | | Unit | Note/Test Condition |
|-------------------------|--------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Total capacitive charge | Q_c | – | 42 | – | nC | $V_R = 400 \text{ V}, di/dt = 200 \text{ A}/\mu\text{s}, I_F \leq I_{F,MAX}, T_j = 150^\circ\text{C}.$ |
| Total Capacitance | C | – | 910 | – | pF | $V_R = 1 \text{ V}, f = 1 \text{ MHz}$ |
| | | – | 117 | – | | $V_R = 300 \text{ V}, f = 1 \text{ MHz}$ |
| | | – | 116 | – | | $V_R = 600 \text{ V}, f = 1 \text{ MHz}$ |

5 Electrical characteristics diagrams

Table 7

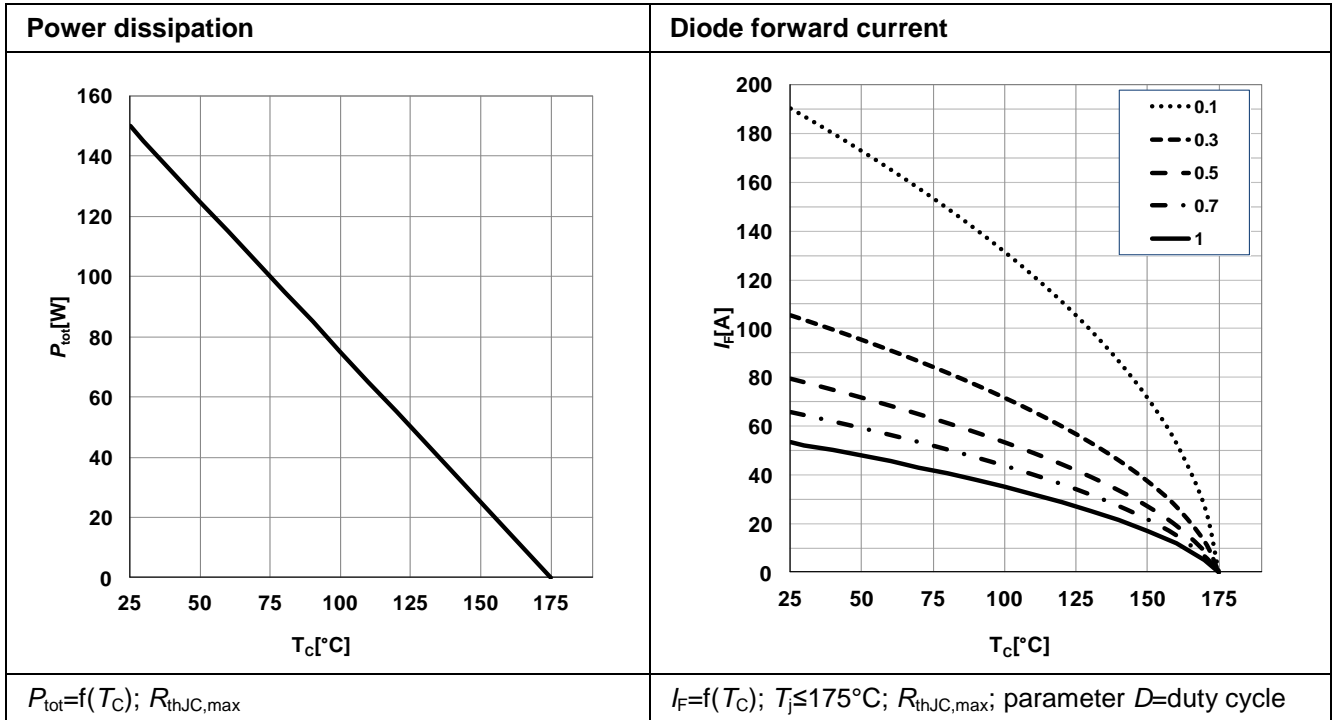


Table 8

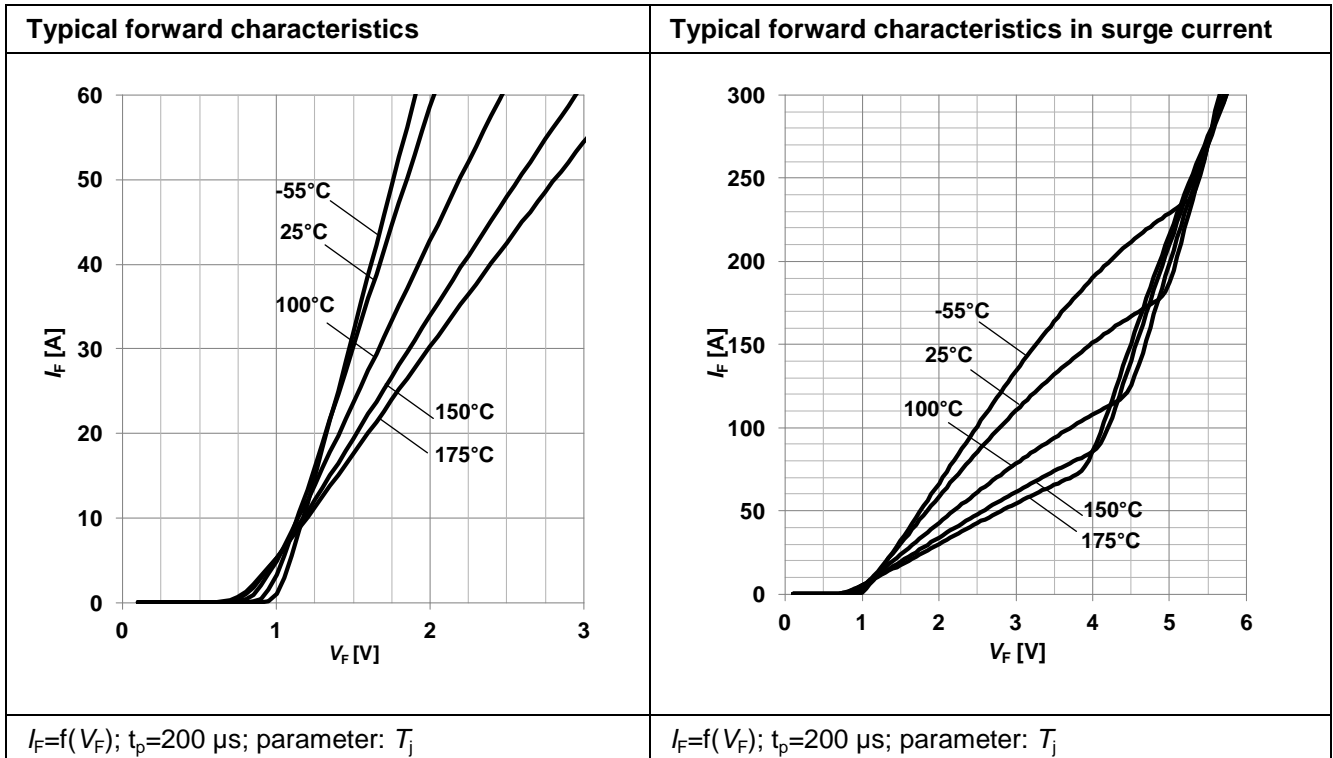
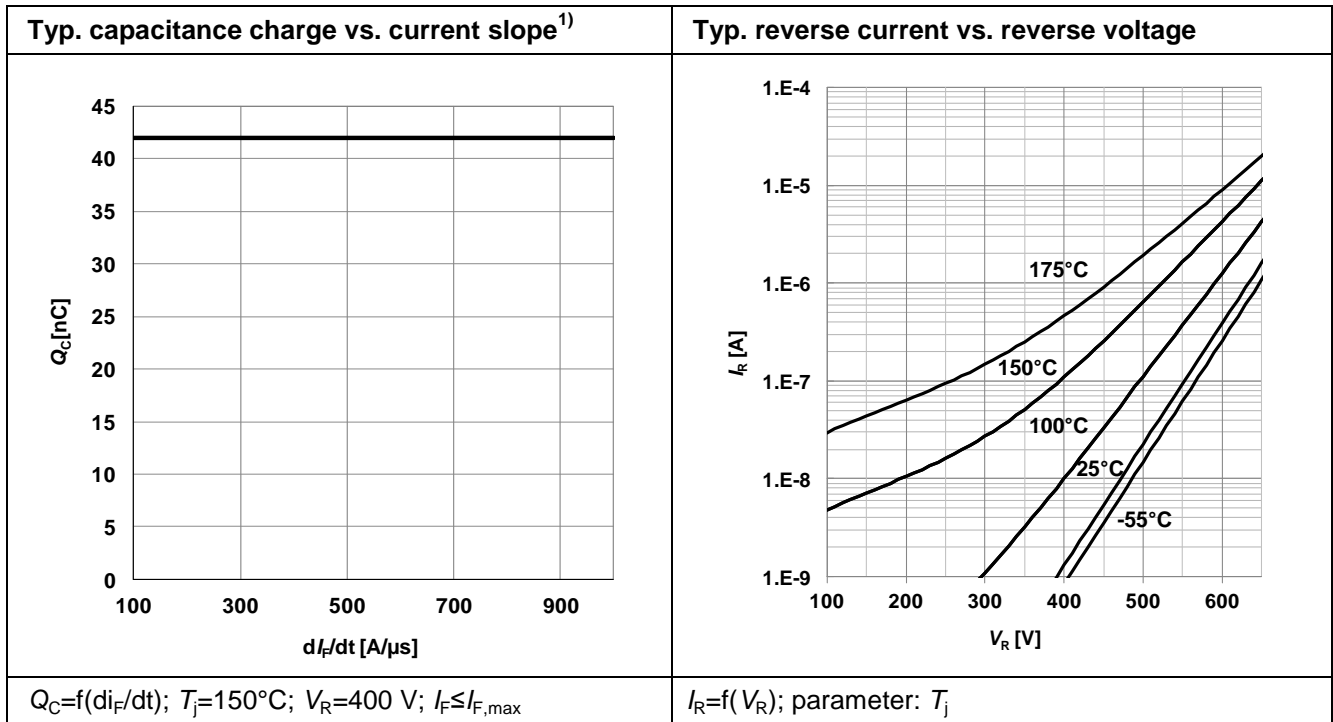


Table 9



1) Only capacitive charge, guaranteed by design.

Table 10

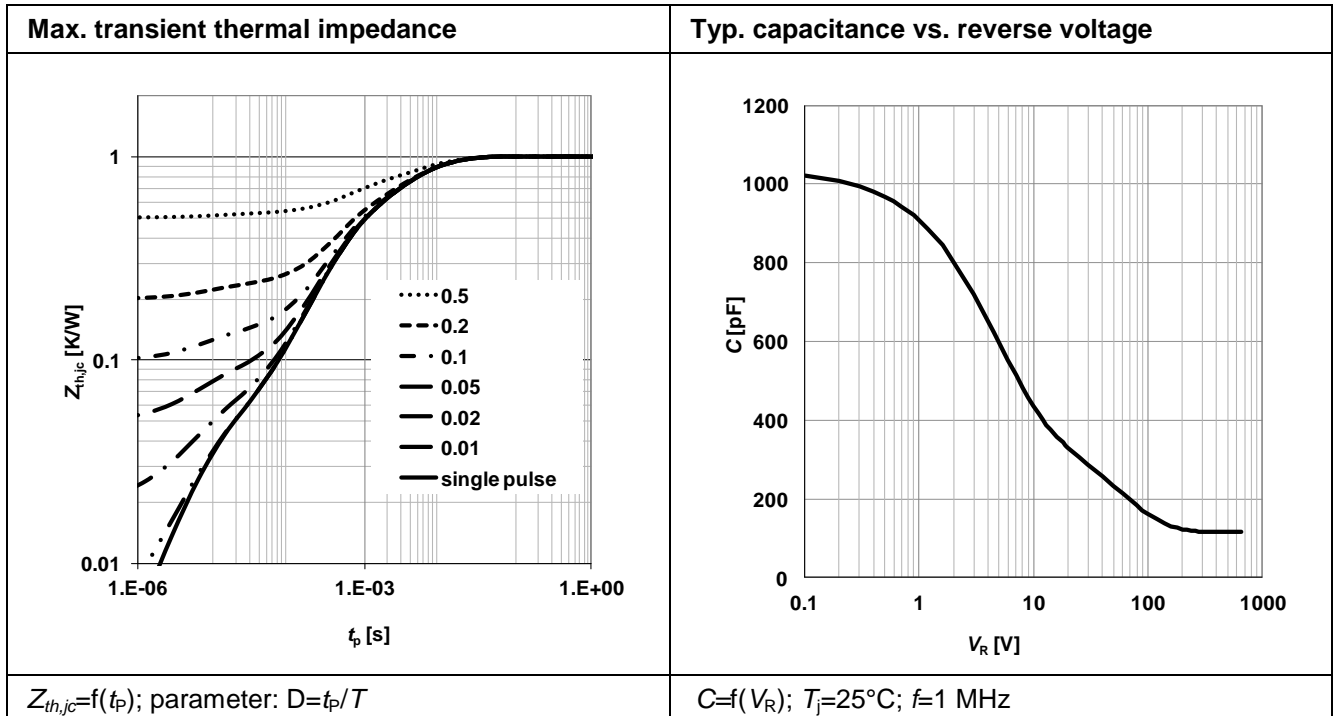
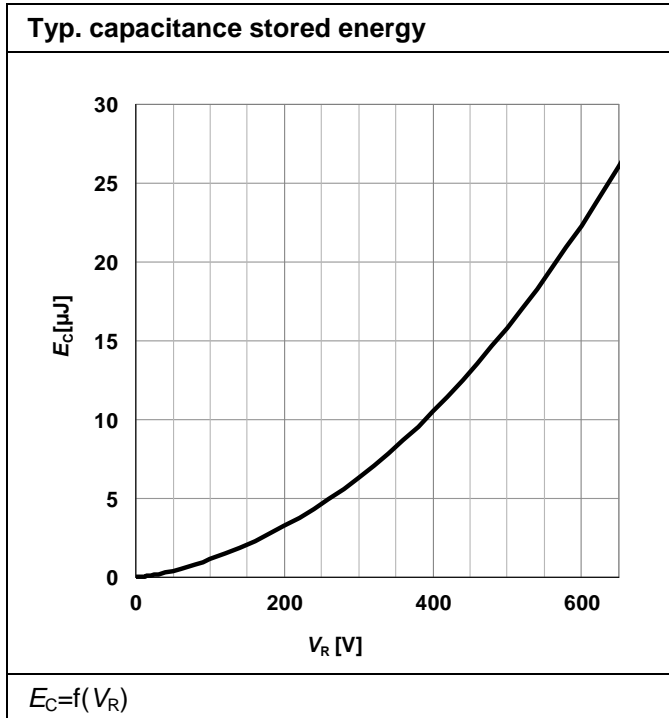


Table 11



6 Package outlines

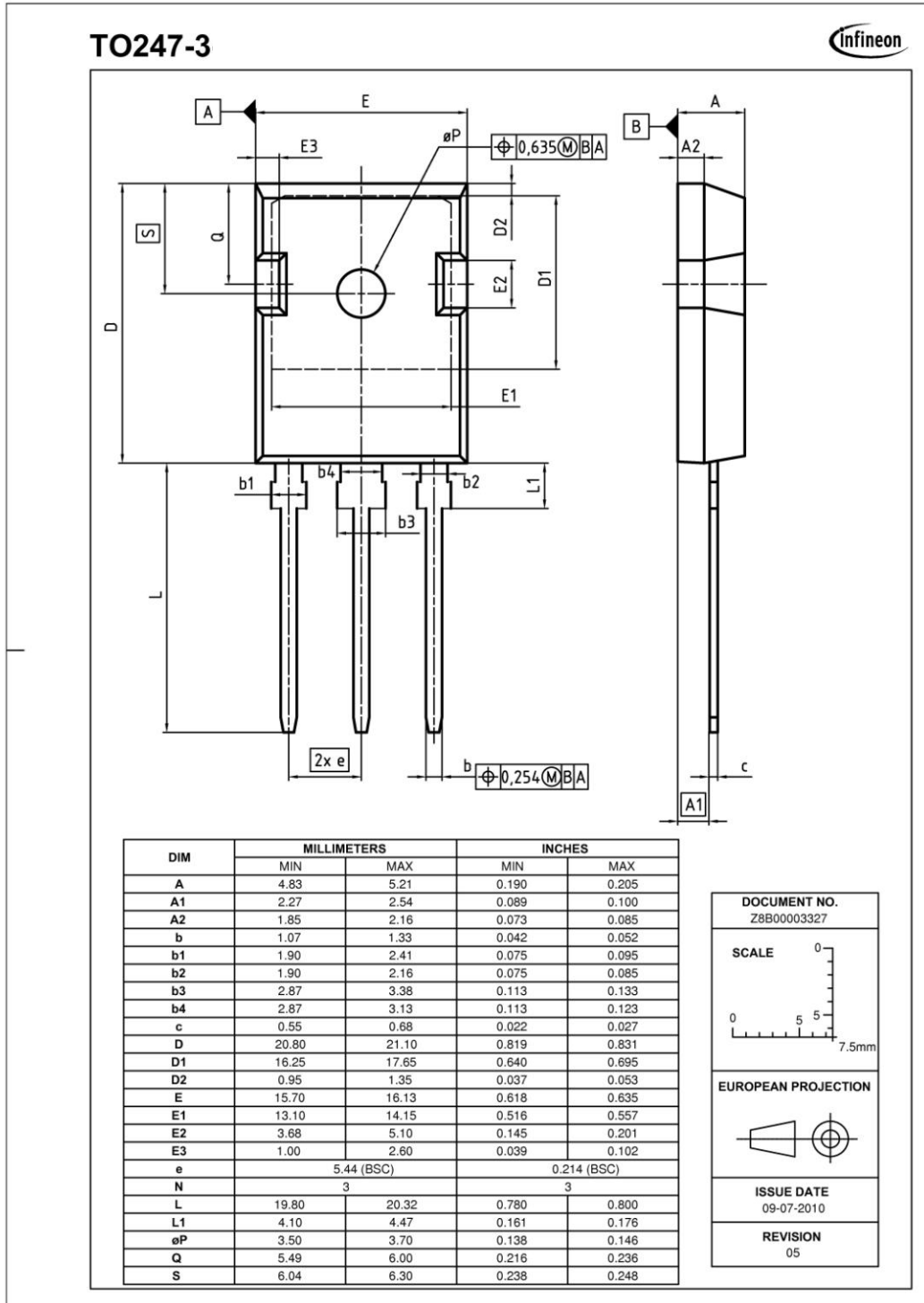


Figure 1 Outlines TO-247, dimensions in mm/inches

7 Revision History

5th. Generation thinQ!™ SiC Schottky Diode

Revision History: 2012-06-28, Rev. 2.0

Previous Revision:

| Revision | Subjects (major changes since last version) |
|----------|---|
| | |
| | |

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